RJP63F3DPP-M0

Silicon N Channel IGBT
High Speed Power Switching

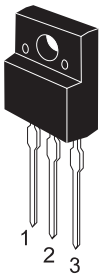
R07DS0321EJ0200
Rev.2.00
May 26, 2011

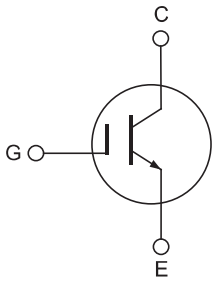
Features

- Trench gate and thin wafer technology (G6H series)
- Low collector to emitter saturation voltage $V_{CE(sat)}$ = 1.7 V typ
- High speed switching tf = 100 ns typ
- Low leak current I_{CES} = 1 μA max
- Isolated package TO-220FL

Outline

RENESAS Package code: PRSS0003AF-A)
(Package name: TO-220FL)





1. Gate
2. Collector
3. Emitter

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to emitter voltage	V_{CES}	630	V
Gate to emitter voltage	V_{GES}	±30	V
Collector current	I_C	40	A
Collector peak current	ic(peak) Note1	200	A
Collector dissipation	P_C Note2	30	W
Junction to case thermal impedance	θj-c	4.17	°C/ W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%
2. Tc = 25°C